



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

US2A THRU US2M

2.0 AMP SURFACE MOUNT HIGH EFFICIENCY RECTIFIERS



FEATURES

- * Ideal for surface mount applications
- * Easy pick and place
- * Built-in strain relief
- * Fast switching speed

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-0 rate flame retardant
- * Metallurgically bonded construction
- * Polarity: Color band denotes cathode end
- * Mounting position: Any
- * Weight: 0.063 grams

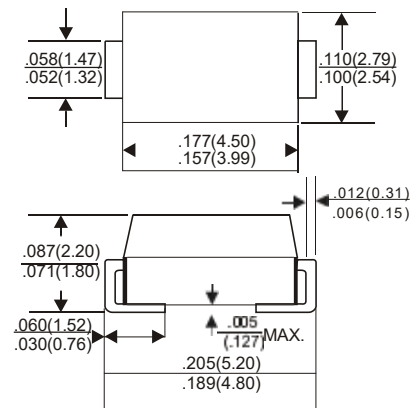
VOLTAGE RANGE

50 to 800 Volts

CURRENT

1.0 Ampere

DO-214AC(SMA)



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25 °C ambient temperature unless otherwise specified.
Single phase half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

TYPE NUMBER	US2A	US2B	US2D	US2E	US2G	US2J	US2K	US2M	UNITS
Maximum Recurrent Peak Reverse Voltage	50	100	200	300	400	600	800	1000	V
Maximum RMS Voltage	35	70	140	210	280	420	560	700	V
Maximum DC Blocking Voltage	50	100	200	300	400	600	800	1000	V
Maximum Average Forward Rectified Current .375"(9.5mm) Lead Length at Ta=50 C	2.0								A
Peak Forward Surge Current, 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	60								A
Maximum Instantaneous Forward Voltage at 2.0A	1.0		1.3		1.85				V
Maximum DC Reverse Current Ta=25°C	5.0								A
at Rated DC Blocking Voltage Ta=100 C	150								µA
Maximum Reverse Recovery Time (Note 1)	50				70				nS
Typical Junction Capacitance (Note 2)	30								pF
Operating and Storage Temperature Range T _J , T _{stg}	-65—+150								°C

NOTES:

1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A
2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

RATING AND CHARACTERISTIC CURVES (US2A THRU US2M)

FIG.1-TYPICAL FORWARD CHARACTERISTICS

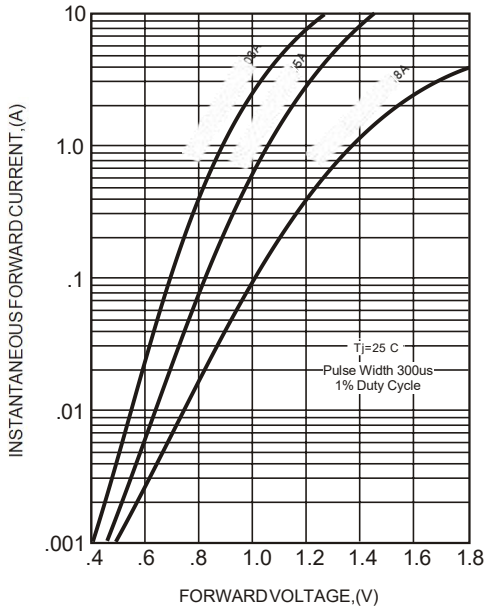


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

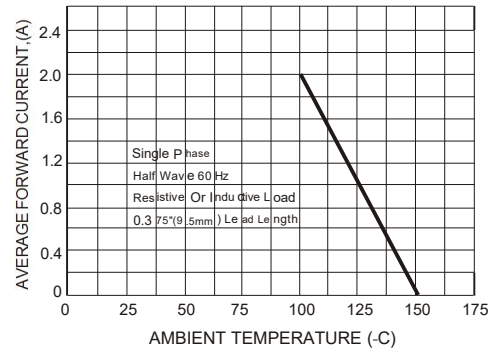
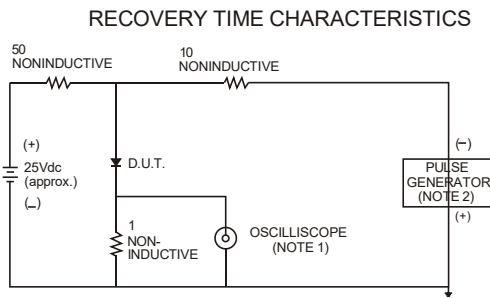


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF.
2. Rise Time= 10ns max., Source Impedance= 50 ohms.

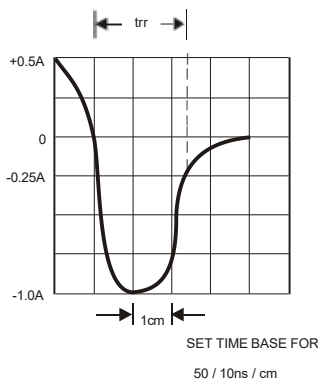


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

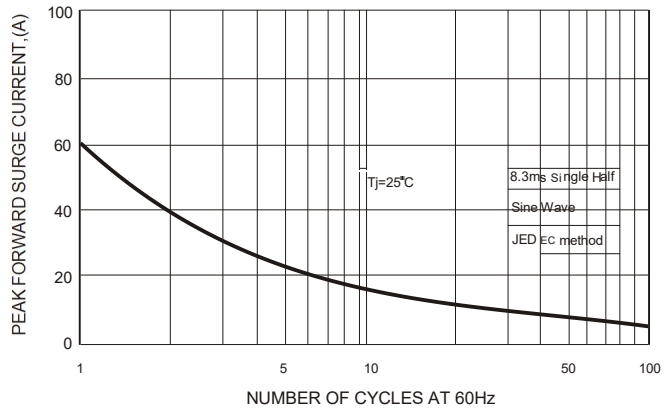


FIG.5-TYPICAL JUNCTION CAPACITANCE

